

### Description

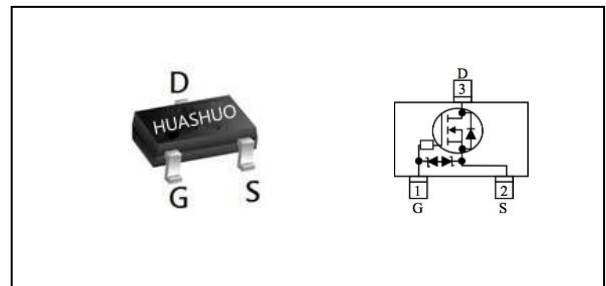
The HSSN3134 is the high cell density trenched N-ch MOSFETs, which provides excellent R<sub>DS(ON)</sub> and efficiency for most of the small power switching and load switch applications. The HSSN3134 meets the RoHS and Green Product requirement with full function reliability approved.

- Fast Switching Speed
- Super Low Gate Charge
- High-Side Switching
- Low Threshold
- ESD Protected up to 2KV

### Product Summary

V <sub>DS</sub>	20	V
R <sub>DS(ON),Max</sub>	200	mΩ
I <sub>D</sub>	1.0	A

### SOT323 Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	20	V
V <sub>GS</sub>	Gate-Source Voltage	±8	V
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 4.5V <sub>1</sub>	1.0	A
I <sub>D</sub> @T <sub>A</sub> =70°C	Continuous Drain Current, V <sub>GS</sub> @ 4.5V <sub>1</sub>	0.75	A
I <sub>DM</sub>	Pulsed Drain Current <sub>2</sub>	4	A
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sub>3</sub>	0.35	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-ambient <sub>1</sub>	---	357	°C/W



**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
B <sub>VDS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	20	---	---	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =1000mA	---	175	200	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =500mA	---	250	300	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	0.5	0.7	1.1	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V	---	---	±100	nA
Q <sub>g</sub>	Total Gate Charge (4.5V)	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =1A	---	1.6	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	0.1	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	0.2	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =10V, V <sub>GS</sub> =4.5V, R <sub>G</sub> =10Ω I <sub>D</sub> =1A	---	5.8	---	ns
T <sub>r</sub>	Rise Time		---	25	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	41	---	
T <sub>f</sub>	Fall Time		---	31	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1MHz	---	92	---	pF
C <sub>oss</sub>	Output Capacitance		---	25	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	9.2	---	

**Diode Characteristics**

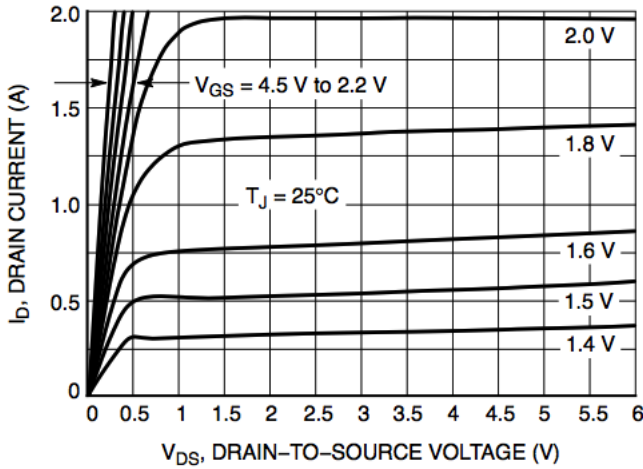
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,4</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	1	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1.2	V

Note :

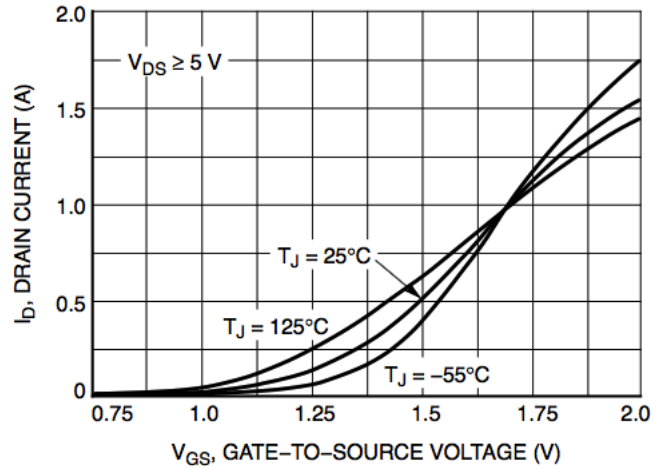
- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.



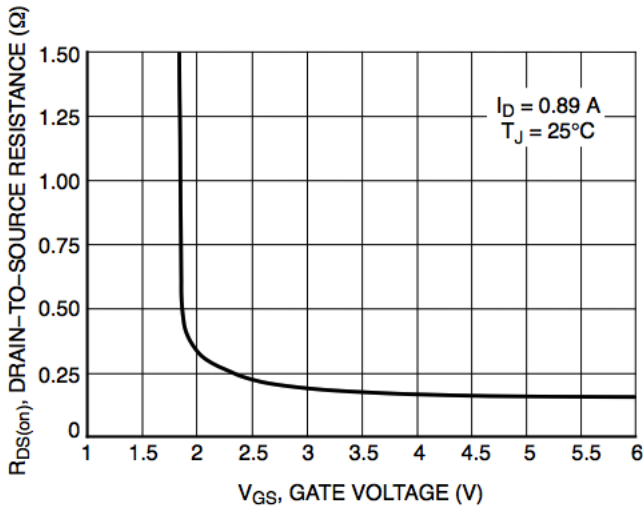
### Typical Characteristics



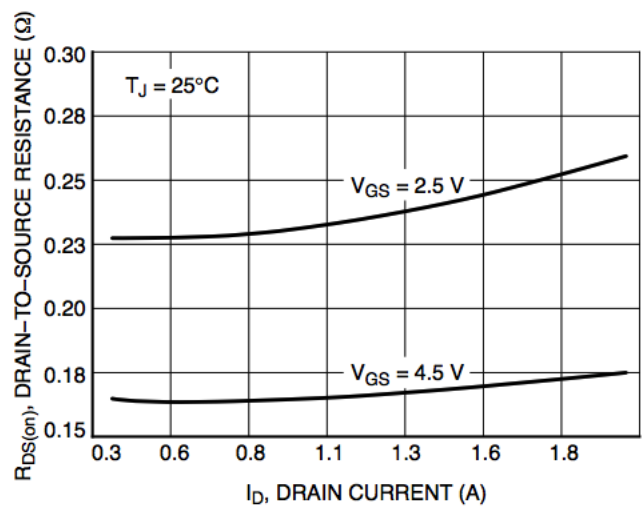
**Figure 1. On-Region Characteristics**



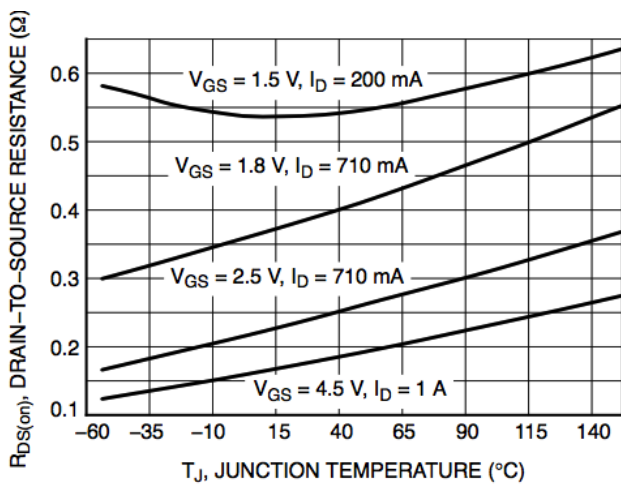
**Figure 2. Transfer Characteristics**



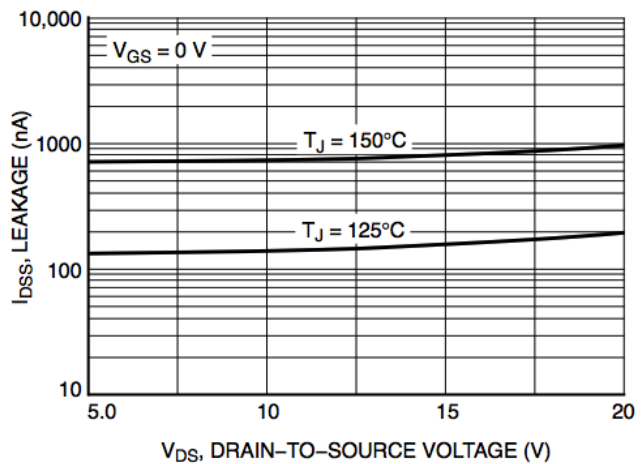
**Figure 3. On-Resistance vs. Gate-to-Source Voltage**



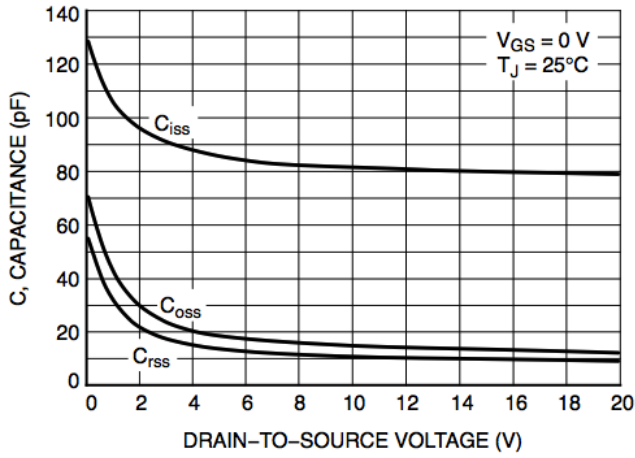
**Figure 4. On-Resistance vs. Drain Current and Gate Voltage**



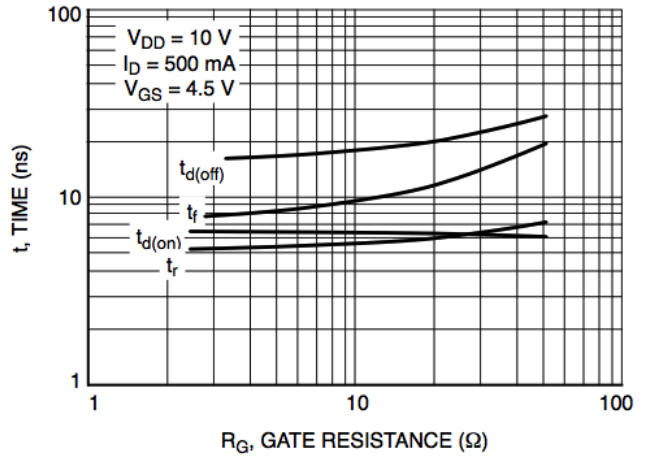
**Figure 5. On-Resistance Variation with Temperature**



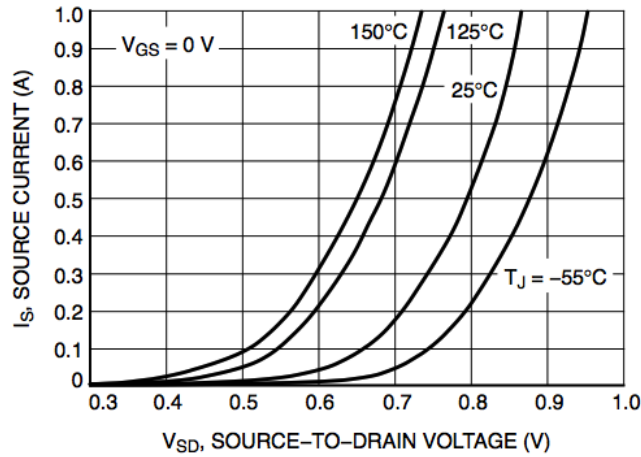
**Figure 6. Drain-to-Source Leakage Current vs. Voltage**



**Figure 7. Capacitance Variation**



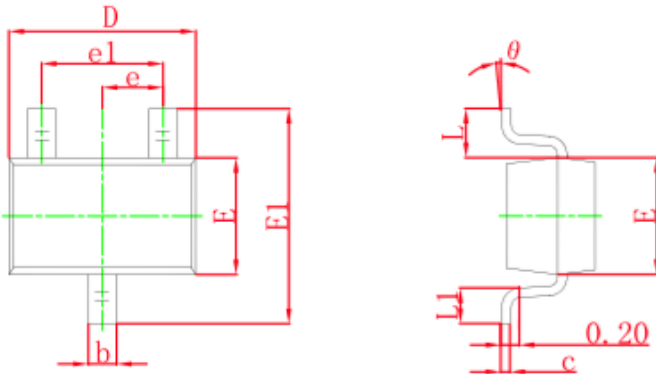
**Figure 8. Resistive Switching Time Variation vs. Gate Resistance**



**Figure 9. Diode Forward Voltage vs. Current**

## Ordering Information

Part Number	Package code	Packaging
HSSN3134	SOT-323	3000/Tape&Reel



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
$\theta$	0°	8°	0°	8°

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